

DESCRIPTION

The CENTRAL SEMICONDUCTOR CMFSH-3i type is a Silicon Dual Isolated Schottky diode designed for surface mount fast switching applications requiring a low forward voltage drop. **Marking Code is C3I.**

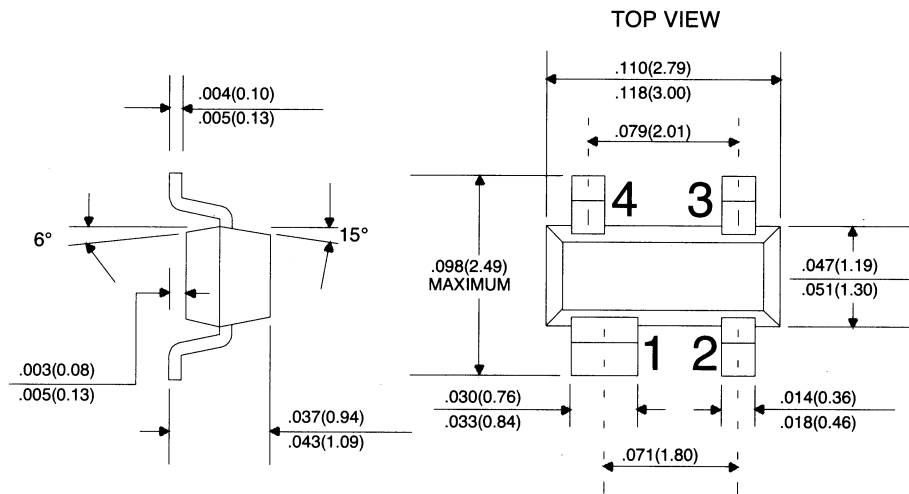
MAXIMUM RATINGS (T_A=25°C)

	SYMBOL		UNITS
Peak Repetitive Reverse Voltage	V _{RRM}	30	V
Continuous Forward Current	I _F	100	mA
Peak Repetitive Forward Current	I _{FRM}	350	mA
Forward Surge Current, t _p =10ms	I _{FSM}	750	mA
Power Dissipation	P _D	350	mW
Operating and Storage			
Junction Temperature	T _J , T _{stg}	-65 to +150	°C
Thermal Resistance	Θ _{JA}	357	°C/W

ELECTRICAL CHARACTERISTICS PER DIODE (T_A=25°C unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
I _R	V _R =25V		90	500	nA
I _R	V _R =25V, T _A =100°C		25	100	μA
BV _R	I _R =100μA	30			V
V _F	I _F =2.0mA		0.29	0.33	V
V _F	I _F =15mA		0.40	0.45	V
V _F	I _F =100mA		0.74	1.00	V
C _T	V _R =1.0V, f=1.0MHz		7.0		pF
t _{rr}	I _F =I _R =10mA, I _{rr} =1.0mA, R _L =100Ω			5.0	ns

All Dimensions in Inches (mm).



LEAD CODE:

- 1) Cathode 1
- 2) Cathode 2
- 3) Anode 2
- 4) Anode 1

DATA
SHEET

R1